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Information System



## On features of potential distribution in avalanche photodiodes with deeply buried pixels

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Funding organisation: Azerbaijan National Academy of Sciences, Institute of Physics, Department of Physical, Mathematical and Technical Sciences Baku (Azerbaijan)

### Abstract

[en] The shape of potential distribution in micro-pixel avalanche photodiodes (MAPD) with deeply buried pixels is investigated. It was found that the electrons created in the photosensitive part of the device are collected to the corresponding n-pixel and multiplied in the avalanche region. At the same time the holes generated in the semiconductor substrate passes through the gaps between the n-pixels and therefore they are not amplified. This results in improvement the both signal/noise ratio and radiation resistance of the device

### Primary Subject

[MATERIALS SCIENCE \(S36\)](#)

### Source

3 figs, 7 refs

### Record Type

Journal Article

<b>Literature Type</b>
Numerical Data
<b>Journal</b>
Fizika (Baku); <a href="#">ISSN 1028-8546</a> ; <a href="#">Worldcat</a> ; v. 19(2); p. 17-19
<b>Country of publication</b>
<a href="#">Azerbaijan</a>
<b>Descriptors (DEI)</b>
<a href="#">AVALANCHE QUENCHING</a> , <a href="#">DATA ANALYSIS</a> , <a href="#">ELECTRIC CONDUCTIVITY</a> , <a href="#">ELECTRIC FIELDS</a> , <a href="#">ELECTRONS</a> , <a href="#">GRADED BAND GAPS</a> , <a href="#">HOLES</a> , <a href="#">NOISE</a> , <a href="#">PHOTODIODES</a> , <a href="#">PHOTONS</a> , <a href="#">PHOTOSENSITIVITY</a> , <a href="#">P-N JUNCTIONS</a> , <a href="#">POTENTIAL FLOW</a> , <a href="#">RADIATION DOSES</a> , <a href="#">SEMICONDUCTOR MATERIALS</a> , <a href="#">SIGNALS</a> , <a href="#">STATISTICAL DATA</a>
<b>Descriptors (DEC)</b>
<a href="#">BOSONS</a> , <a href="#">DATA</a> , <a href="#">DOSES</a> , <a href="#">ELECTRICAL PROPERTIES</a> , <a href="#">ELEMENTARY PARTICLES</a> , <a href="#">FERMIONS</a> , <a href="#">FLUID FLOW</a> , <a href="#">INFORMATION</a> , <a href="#">LEPTONS</a> , <a href="#">MASSLESS PARTICLES</a> , <a href="#">MATERIALS</a> , <a href="#">NUMERICAL DATA</a> , <a href="#">PHYSICAL PROPERTIES</a> , <a href="#">SEMICONDUCTOR DEVICES</a> , <a href="#">SEMICONDUCTOR DIODES</a> , <a href="#">SEMICONDUCTOR JUNCTIONS</a> , <a href="#">SENSITIVITY</a>
<b>Publication Year</b>
<a href="#">2013</a>
<b>Language</b>
<a href="#">English</a>
<b>Reference Number</b>
<a href="#">45046629</a>
<b>INIS Volume</b>
<a href="#">45</a>
<b>INIS Issue</b>
<a href="#">19</a>